

SKKT 250, SKKH 250



SEMIPACK® 3

Thyristor / Diode Modules

SKKH 250
SKKT 250

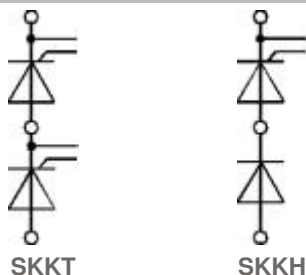
Features

- Heat transfer through aluminium nitride ceramic isolated metal baseplate
- Precious metal pressure contacts for high reliability
- Thyristor with amplifying gate
- UL recognized, file no. E 63 532

Typical Applications

- DC motor control (e. g. for machine tools)
- AC motor starters
- Temperature control (e. g. for ovens, chemical processes)
- Professional light dimming (studios, theaters)

1) See the assembly instructions
2) The screws must be lubricated



V_{RSM} V	V_{RRM}, V_{DRM} V	$I_{TRMS} = 420$ A (maximum value for $I_{TAV} = 250$ A (sin. 180; 1
900	800	SKKT 250/08E
1300	1200	SKKT 250/12E
1500	1400	SKKT 250/14E
1700	1600	SKKT 250/16E
1900	1800	SKKT 250/18E
		SKKH 250/12
		SKKH 250/14
		SKKH 250/16
		SKKH 250/18

Symbol	Conditions
I_{TAV}	sin. 180; $T_c = 85$ (100) °C;
I_D	P16/200F; $T_a = 35$ °C; B2/B6
I_{RMS}	P16/200F; $T_a = 35$ °C; W1 / W3
I_{TSM}	$T_{vj} = 25$ °C; 10 ms $T_{vj} = 130$ °C; 10 ms
$i_{\beta t}$	$T_{vj} = 25$ °C; 8,3 ... 10 ms $T_{vj} = 130$ °C; 8,3 ... 10 ms
V_T	$T_{vj} = 25$ °C; $I_T = 750$ A
$V_{T(TO)}$	$T_{vj} = 130$ °C
r_T	$T_{vj} = 130$ °C
$I_{DD}; I_{RD}$	$T_{vj} = 130$ °C; $V_{RD} = V_{RRM}; V_{DD} = V_{DRM}$
t_{gd}	$T_{vj} = 25$ °C; $I_G = 1$ A; $di_G/dt = 1$ A/μs
t_{gr}	$V_D = 0,67 * V_{DRM}$
$(di/dt)_{cr}$	$T_{vj} = 130$ °C
$(dv/dt)_{cr}$	$T_{vj} = 130$ °C
t_q	$T_{vj} = 130$ °C
I_H	$T_{vj} = 25$ °C; typ. / max.
I_L	$T_{vj} = 25$ °C; $R_G = 33$ Ω; typ. / max.
V_{GT}	$T_{vj} = 25$ °C; d.c.
I_{GT}	$T_{vj} = 25$ °C; d.c.
V_{GD}	$T_{vj} = 130$ °C; d.c.
I_{GD}	$T_{vj} = 130$ °C; d.c.
$R_{th(j-c)}$	cont.; per thyristor / per module
$R_{th(j-c)}$	sin. 180; per thyristor / per module
$R_{th(j-c)}$	rec. 120; per thyristor / per module
$R_{th(c-s)}$	per thyristor / per module
T_{vj}	
T_{stg}	
V_{isol}	a. c. 50 Hz; r.m.s.; 1 s / 1 min.
M_s	to heatsink
M_t	to terminals
a	
m	approx.
Case	SKKT SKKH

Diagrams

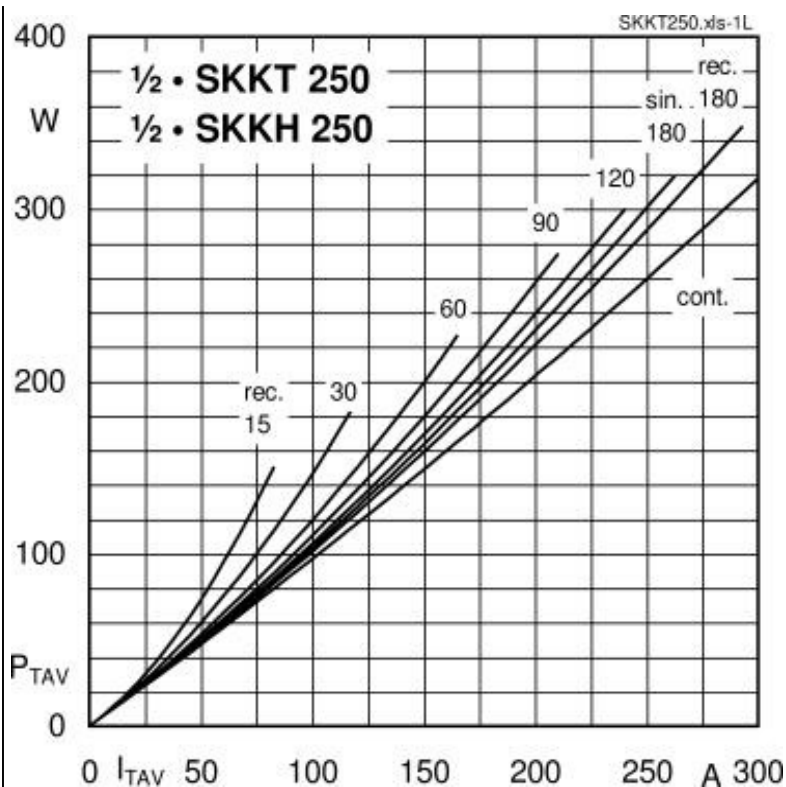


Fig. 1L Power dissipation per thyristor vs. on-state current

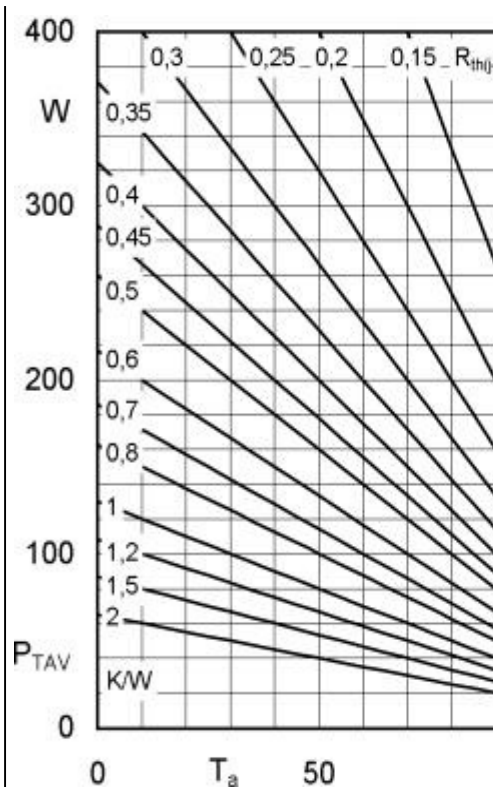


Fig. 1R Power dissipation per thyristor vs. amb

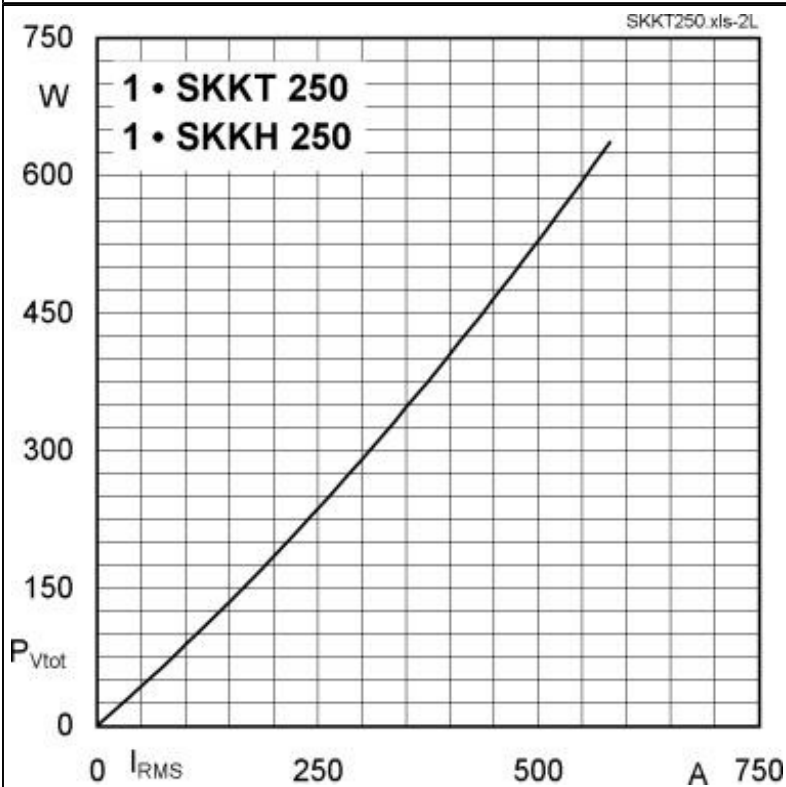


Fig. 2L Power dissipation per module vs. rms current

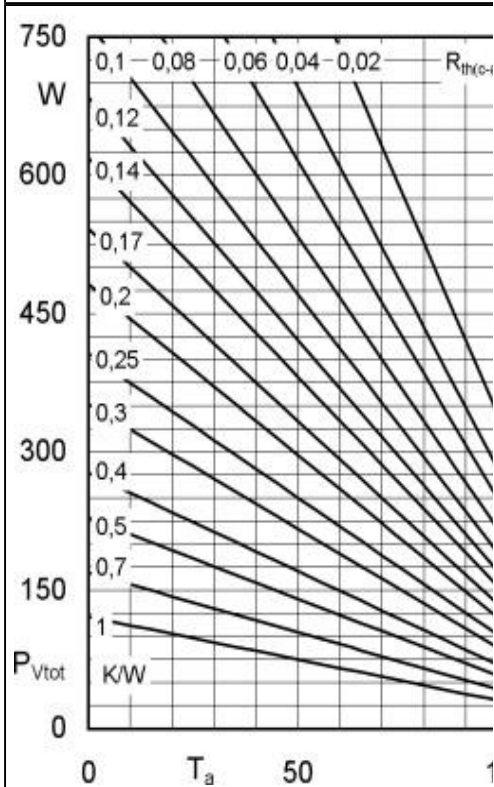


Fig. 2R Power dissipation per module vs. cas

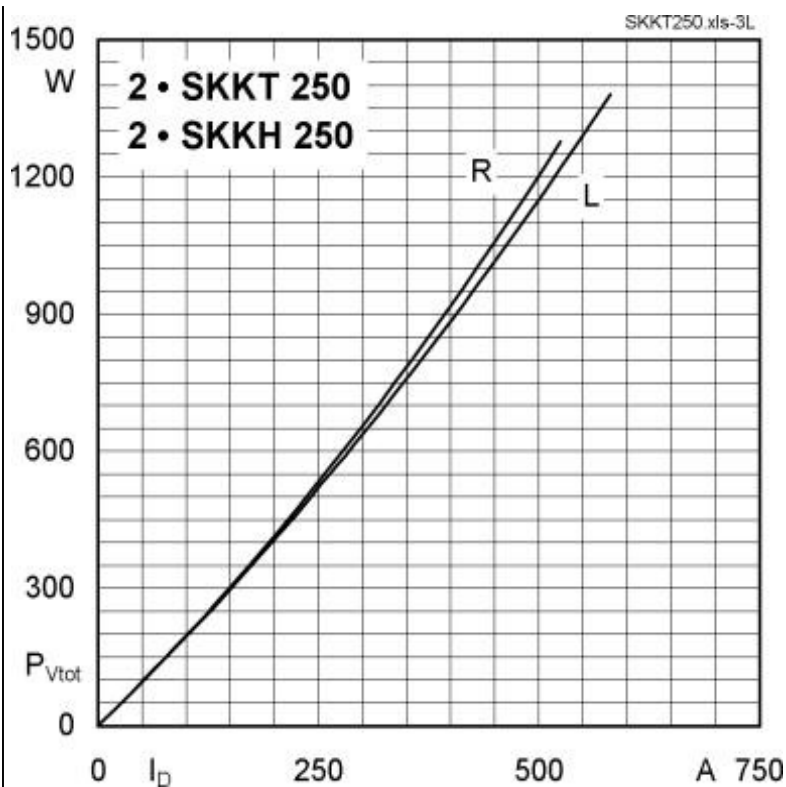


Fig. 3L Power dissipation of two modules vs. direct current

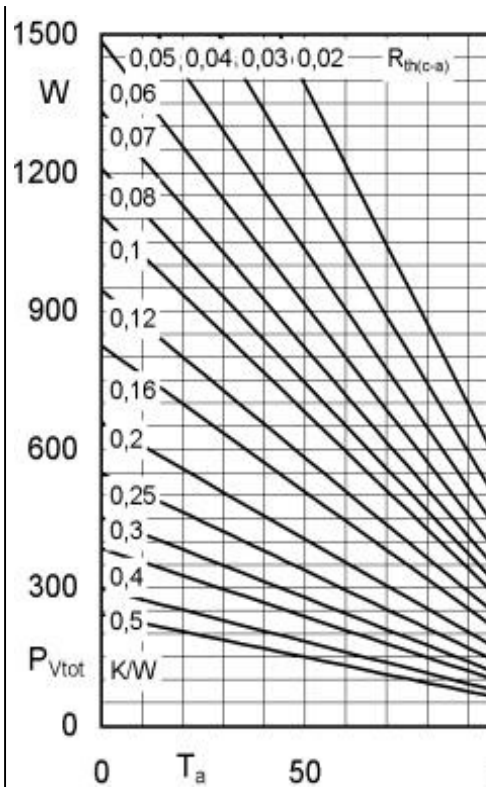


Fig. 3R Power dissipation of two modules vs. ambient temperature

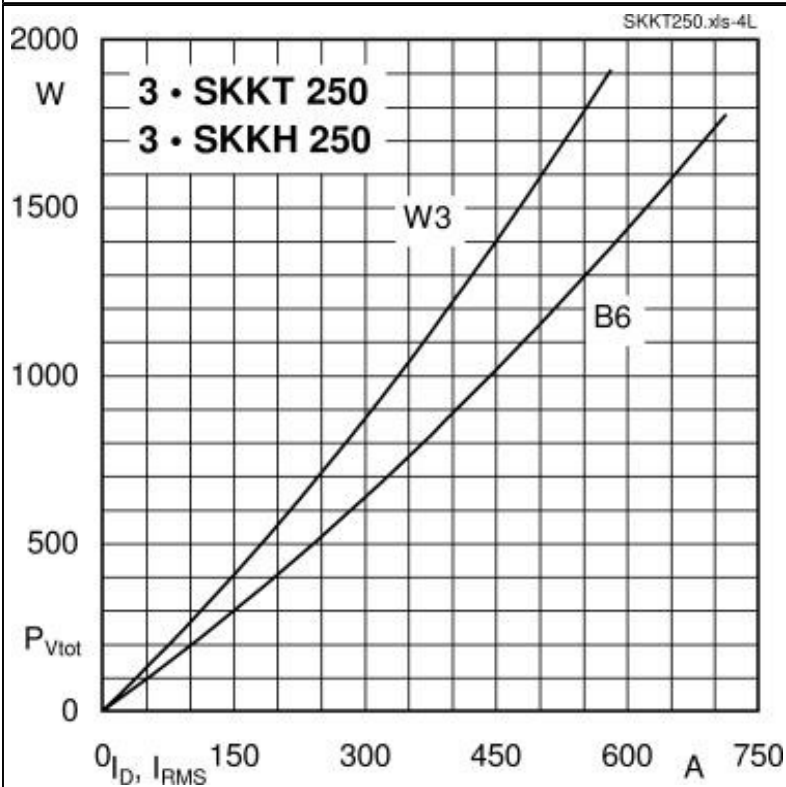


Fig. 4L Power dissipation of three modules vs. direct and rms current

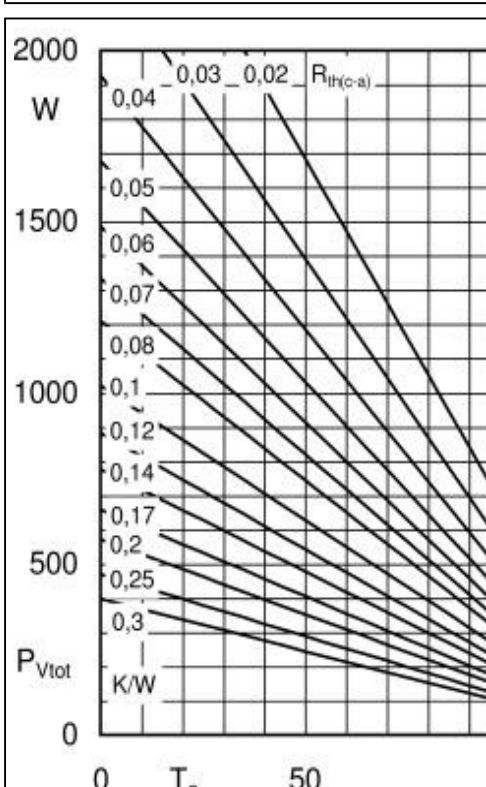


Fig. 4R Power dissipation of three modules vs. ambient temperature

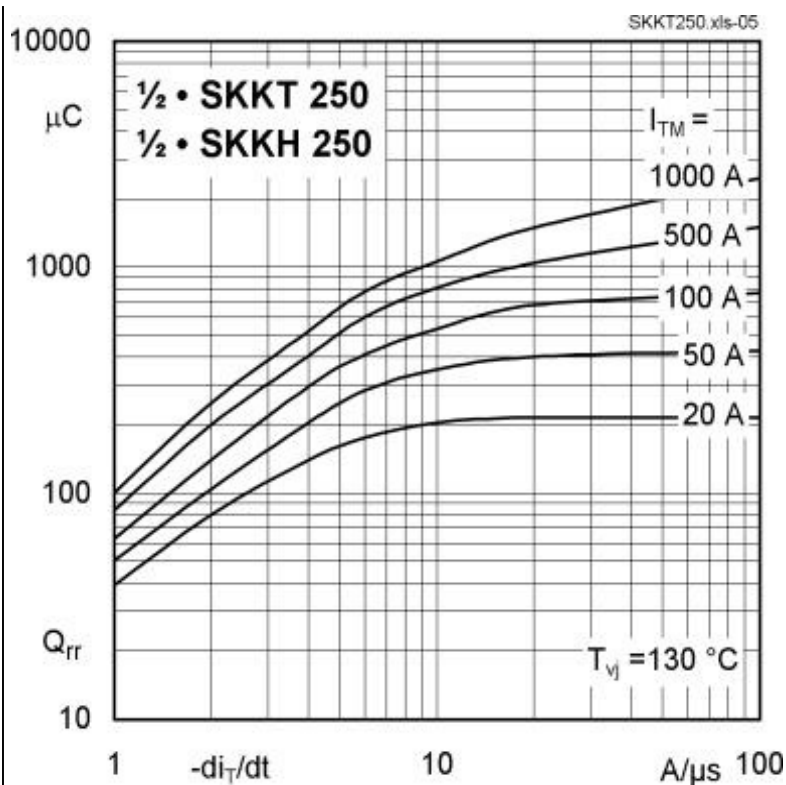


Fig. 5 Recovered charge vs. current decrease

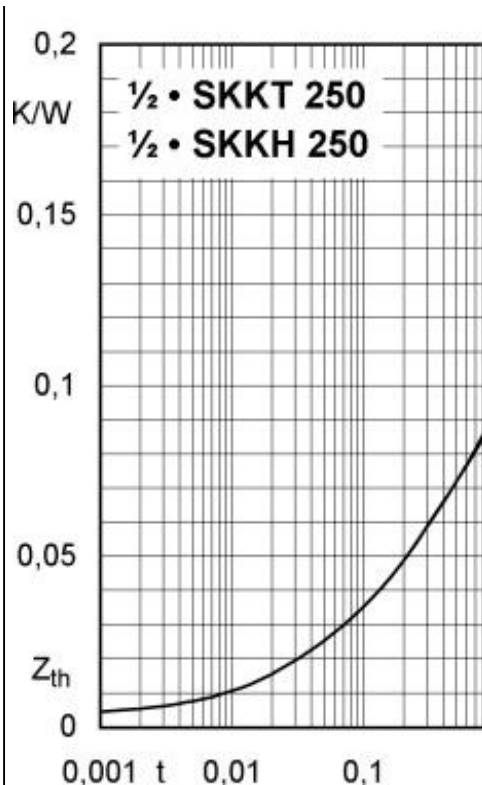


Fig. 6 Transient thermal impedance vs. time

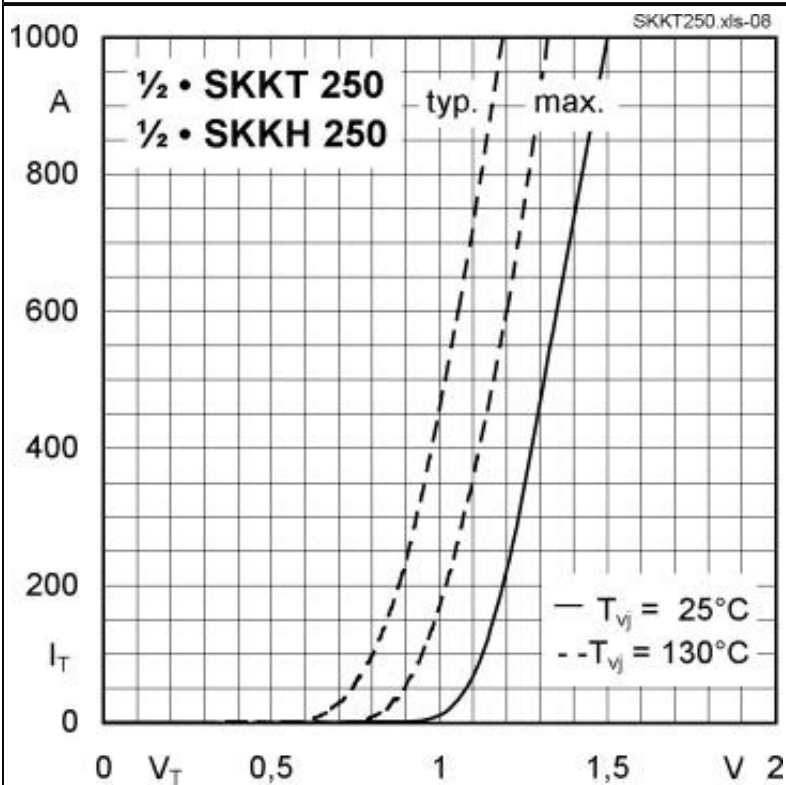


Fig. 7 On-state characteristics

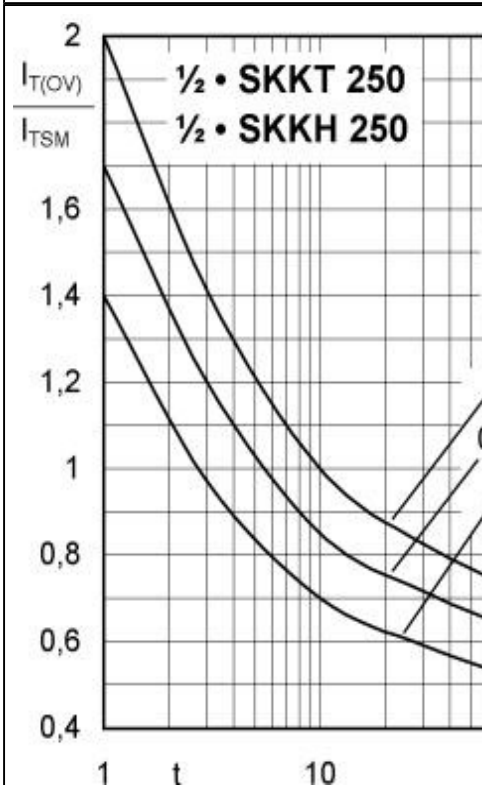


Fig. 8 Surge overload current vs. time

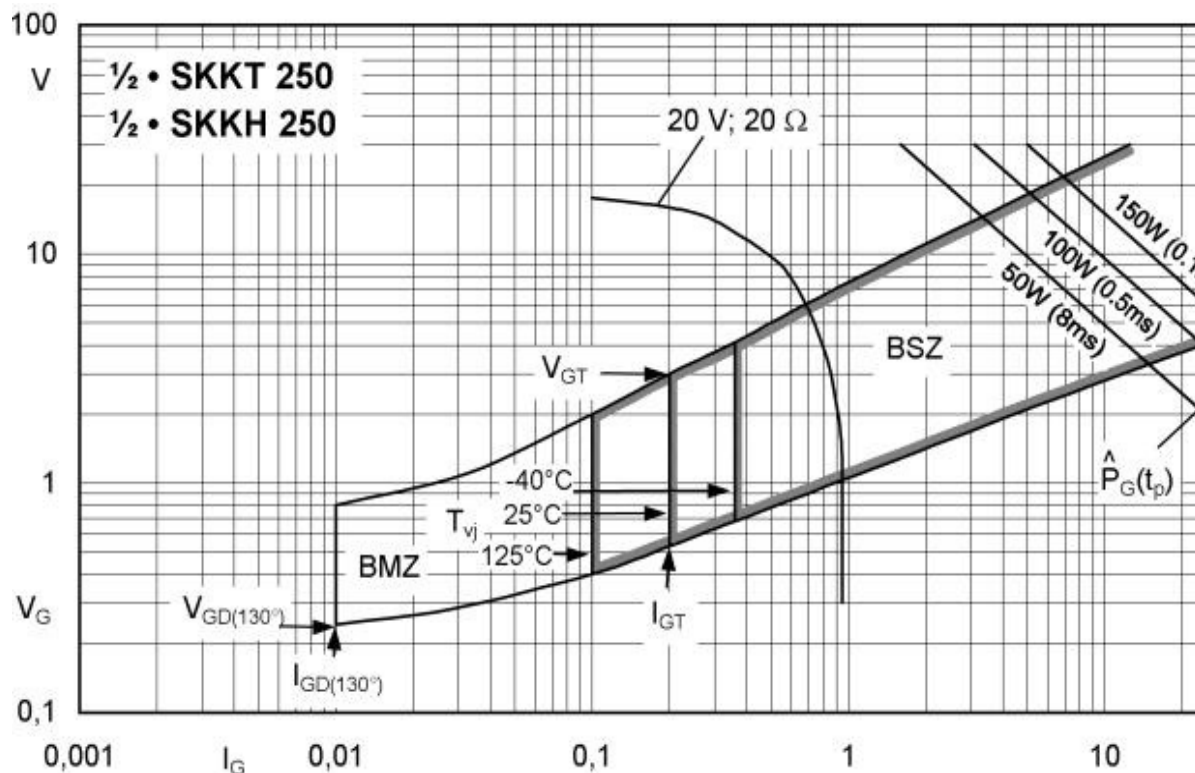
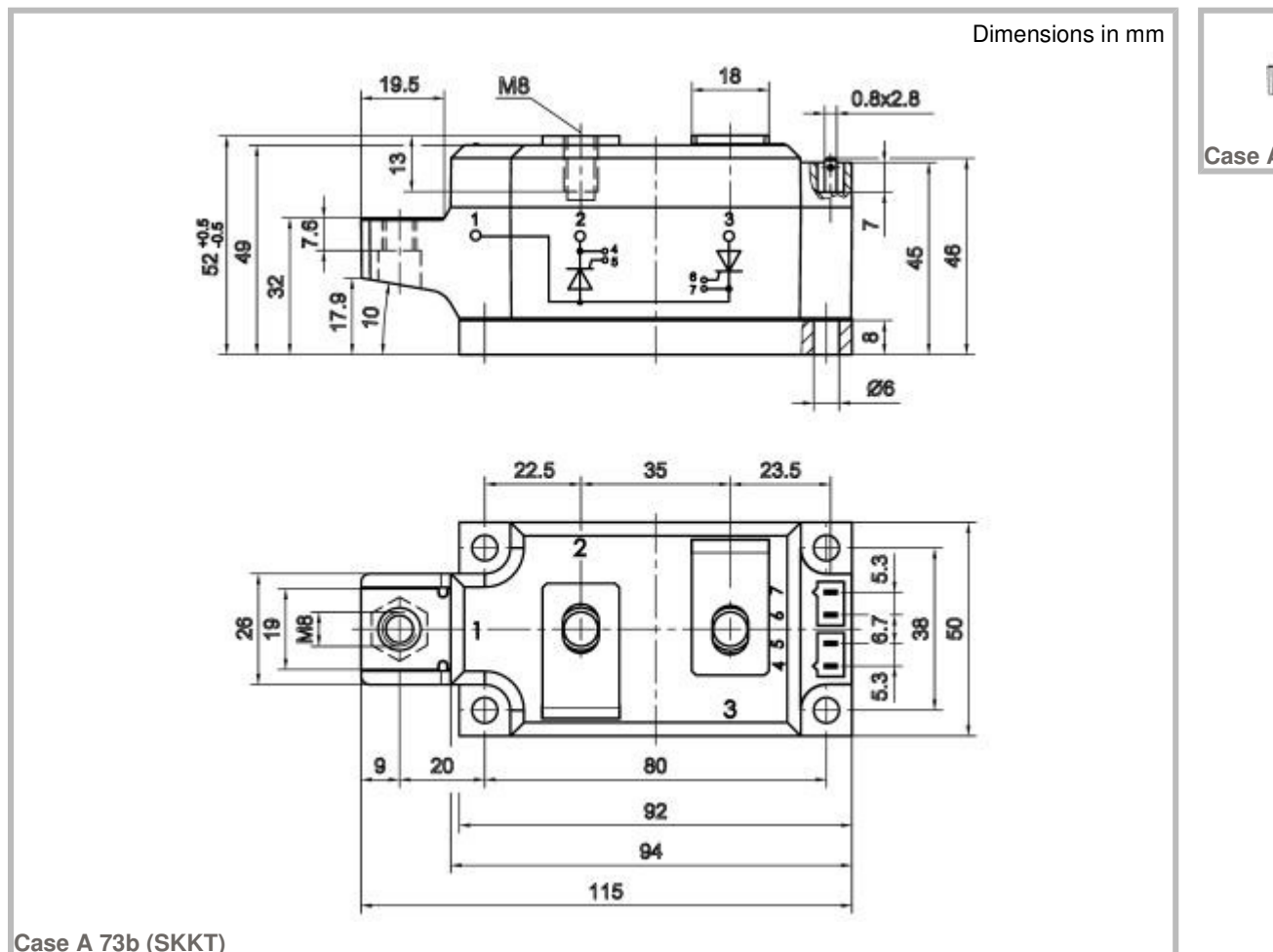


Fig. 9 Gate trigger characteristics

Cases / Circuits



This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee expressed or implied performance or suitability.